

**Honeywell**  
**ACCUSPIN<sup>®</sup> Antimony**  
**(Sb-532) Spin-on Dopant**

# Honeywell ACCUSPIN® Antimony (Sb-532) Spin-on Dopant

## POLYMER FOR N-TYPE BURIED LAYER DIFFUSION

### BENEFITS

- Industry proven performance in bipolar devices
- Lower maintenance costs than antimony trioxide solid sources
- Better control of sheet resistance non-uniformity to within 1% within a wafer and 2% wafer to wafer
- Safer to handle and use than solid antimony sources

### OVERVIEW

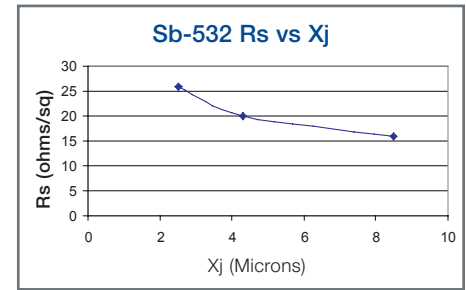
The ACCUSPIN Sb-532 Spin-on dopant is an antimony doped silicon oxide polymer designed for n-type buried layer diffusion. ACCUSPIN Sb-532 has been in large volume IC production for over 25 years.

Sb-532 can be applied using standard spin coaters. ACCUSPIN Sb-532 Spin-on dopant reduces the need for costly diffusion furnace tube cleaning or replacement required when using antimony trioxide dopants. ACCUSPIN Sb-532 materials also reduce any auto-doping from the furnace walls.

Because ACCUSPIN Sb-532 Spin-on dopant is an antimony bonded silicate polymer, diffusion is more uniform during the drive-in process so sheet resistance and junction depths are repeatable. The Spin-on process eliminates sheet resistance non-uniformity issues due to changes in gas flows of arsine or arsenic trioxide vaporization sources and wafer placement in the diffusion furnace.

### FEATURES

#### Sheet Resistance vs Junction Depth



#### Thickness

Product	Thickness
Sb-532	800Å

#### Material Properties

Sb-532 Shelf Life @ 0-4°C: 6 months  
Bottle Sizes Available  
125ml, 250ml, 500ml, 1L, 4L



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OUR COMMITMENT TO SUSTAINABILITY

#### Honeywell Electronic Materials

USA: 1-509-252-2102

China: 86-21-28942481

Germany: 49-5137-999-9199

Japan: 81-3-6730-7092

Korea: 82-2-3483-5076

Singapore: 65-6580-3593

Taiwan: 886-3-6580300 ext.312

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